



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638

ysbdt@szyoushang.cn

www.szyoushang.cn



企业微信二维码



企业QQ二维码

Product Summary

BV_{DSS}	$R_{DS(ON)} \text{ max}$	I_D $T_A = +25^\circ\text{C}$
30V	18.6m Ω @ $V_{GS} = 10\text{V}$	8.0A
	26.5m Ω @ $V_{GS} = 4.5\text{V}$	6.5A

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

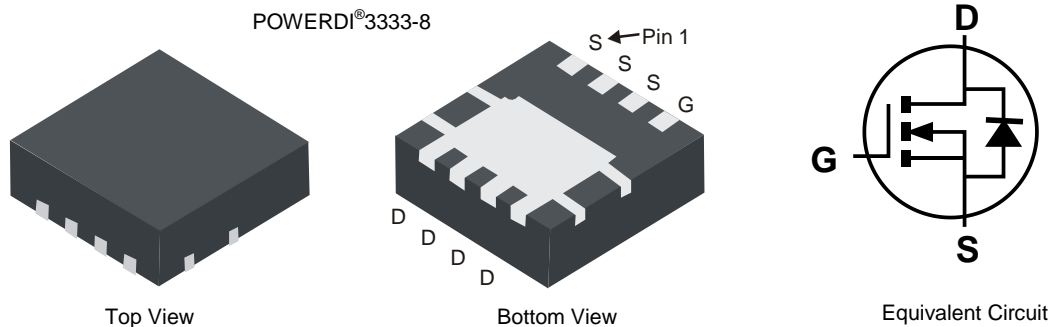
- Backlighting
- DC-DC Converters
- Power Management Functions

Features

- Low $R_{DS(ON)}$ – ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- 100% UIS (Avalanche) Rated
- 100% R_g Tested

Mechanical Data

- Case: POWERDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ^(E3)
- Weight: 0.072 grams (Approximate)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 5) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	5.3	A
		T _A = +70°C		4.2	
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C	I _D	8.0	A
		T _A = +70°C		6.3	
Continuous Drain Current (Note 6) V _{GS} = 10V	t ≤ 10s	T _A = +25°C T _A = +70°C	I _D	9.5 7.7	A
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	T _A = +25°C	I _D	6.5	A
		T _A = +70°C		4.9	
Continuous Drain Current (Note 6) V _{GS} = 4.5V	t ≤ 10s	T _A = +25°C	I _D	7.8	A
		T _A = +70°C		6.2	
Pulsed Drain Current (Note 7)			I _{DM}	70	A
Avalanche Current (Notes 7 & 8)			I _{AR}	18	A
Repetitive Avalanche Energy (Notes 7 & 8) L = 0.1mH			E _{AR}	16	mJ

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	P _D	1.0	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	R _{θJA}	130.6	°C/W
Power Dissipation (Note 6)	P _D	2.07	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	R _{θJA}	62.5	°C/W
Power Dissipation (Note 6) t ≤ 10s	P _D	3.0	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6) t ≤ 10s	R _{θJA}	43.8	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

- Notes:
5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
 6. Device mounted on 2" x 2" FR-4 PCB with high coverage 2 oz. Copper, single sided.
 7. Repetitive rating, pulse width limited by junction temperature.
 8. I_{AR} and E_{AR} rating are based on low frequency and duty cycles to keep T_J = +25°C.

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	100	nA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±25V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	0.9	1.2	1.8	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	-	13.5	18.6	mΩ	V _{GS} = 10V, I _D = 10A
		-	22	26.5		V _{GS} = 4.5V, I _D = 7.5A
Diode Forward Voltage	V _{SD}	-	0.7	1.0	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	-	580	-	pF	V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	110	-		
Reverse Transfer Capacitance	C _{rss}	-	70	-		
Gate Resistance	R _g	-	2.0	3.0	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge V _{GS} = 4.5V	Q _g	-	5.3	-	nC	V _{GS} = 4.5V, V _{DS} = 15V, I _D = 10A
Total Gate Charge V _{GS} = 10V	Q _g	-	11.3	-		
Gate-Source Charge	Q _{gs}	-	1.9	-		
Gate-Drain Charge	Q _{gd}	-	1.9	-		
Turn-On Delay Time	t _{D(ON)}	-	4.4	-	ns	V _{GS} = 10V, V _{DS} = 15V, R _L = 15Ω, R _G = 6Ω
Turn-On Rise Time	t _R	-	4.6	-	ns	
Turn-Off Delay Time	t _{D(OFF)}	-	19.5	-	ns	
Turn-Off Fall Time	t _F	-	5.8	-	ns	

- Notes:
9. Short duration pulse test used to minimize self-heating effect.
 10. Guaranteed by design. Not subject to production testing.

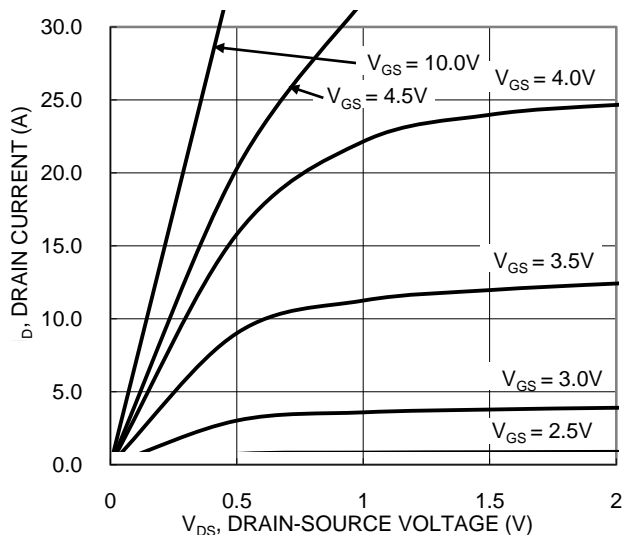


Figure 1. Typical Output Characteristic

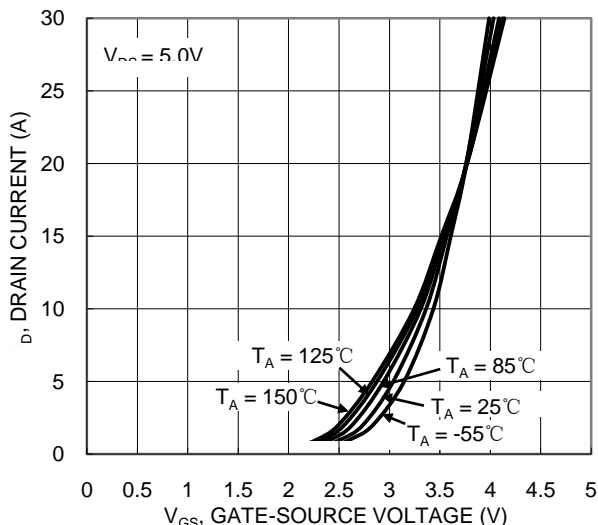


Figure 2. Typical Transfer Characteristic

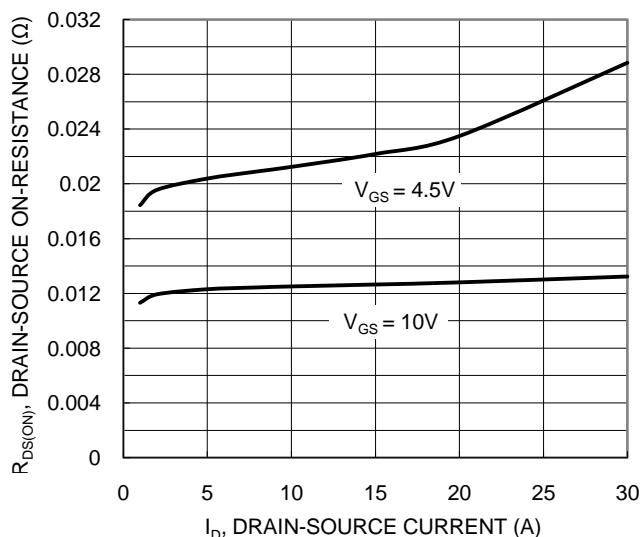


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

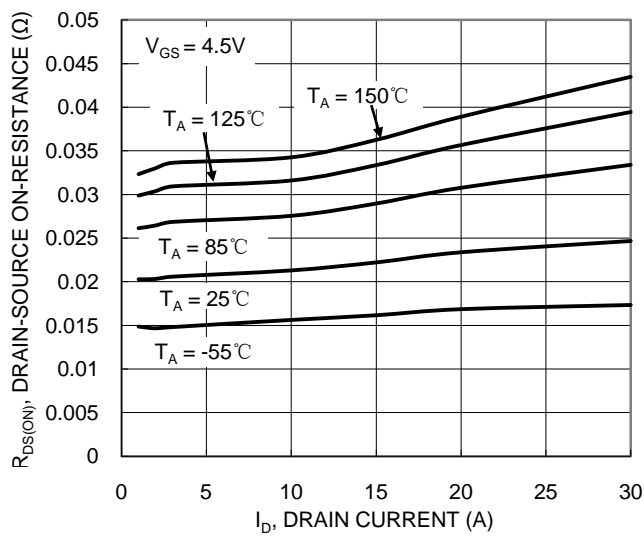


Figure 4. Typical On-Resistance vs. Drain Current and Temperature

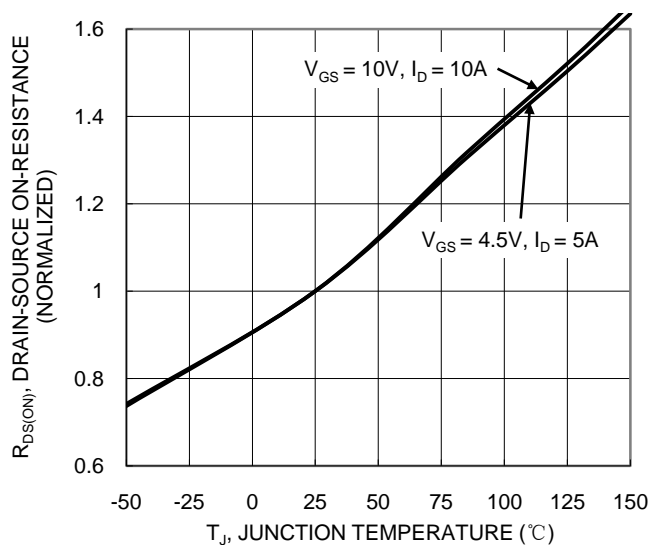


Figure 5. On-Resistance Variation with Temperature

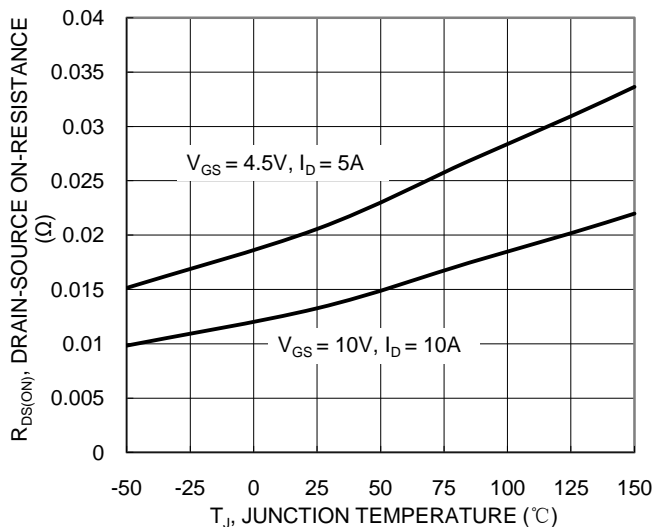


Figure 6. On-Resistance Variation with Temperature

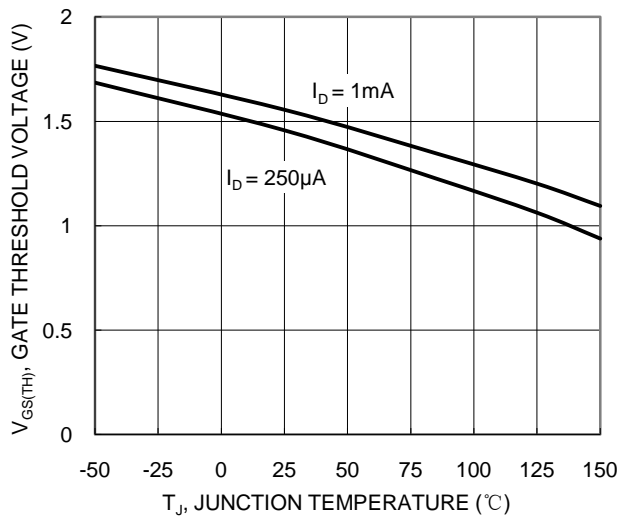


Figure 7. Gate Threshold Variation vs. Temperature

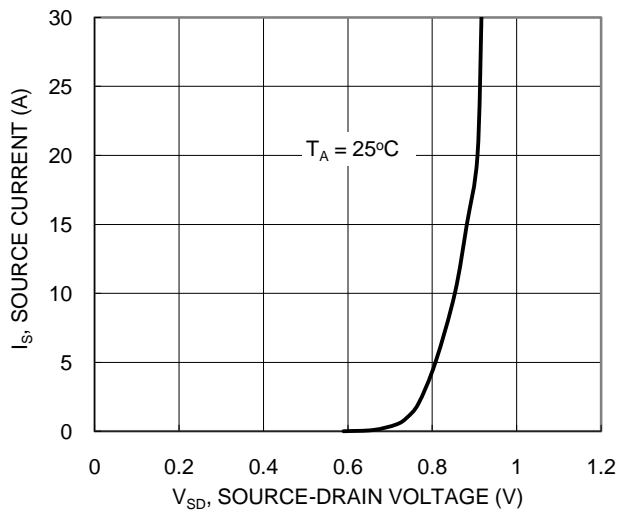


Figure 8. Diode Forward Voltage vs. Current

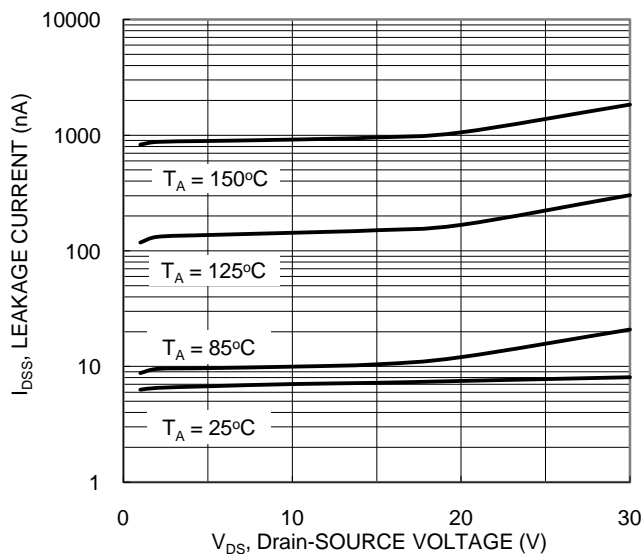


Figure 9. Typical Leakage Current vs. Drain-Source Voltage

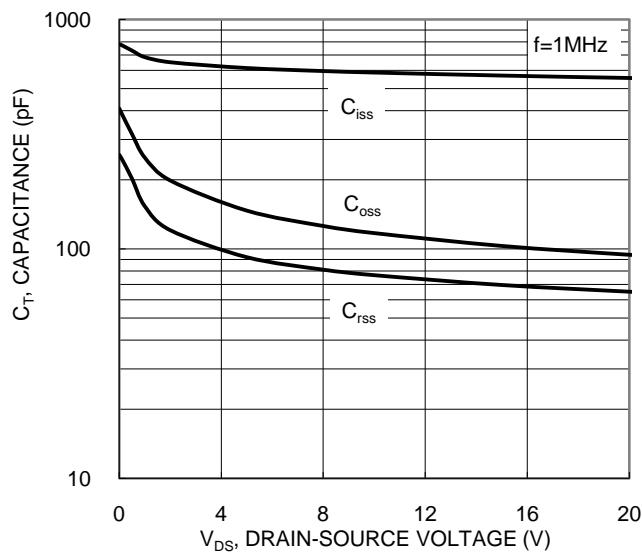


Figure 10. Typical Total Capacitance

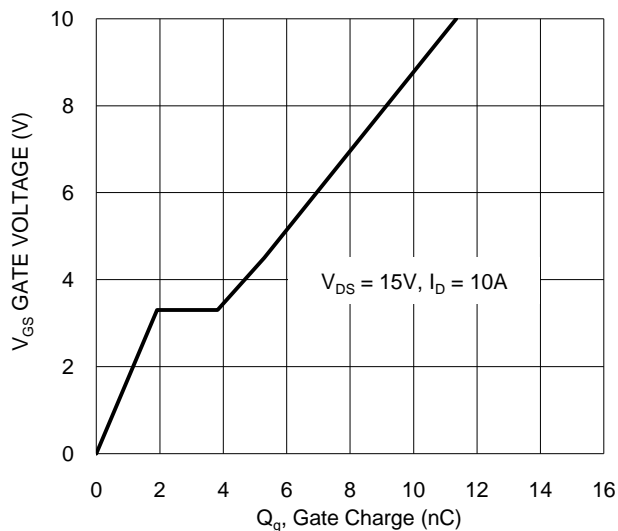


Figure 11. Gate Charge

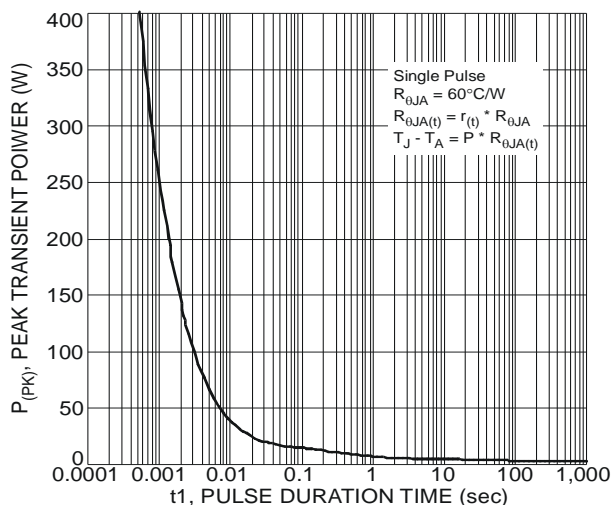
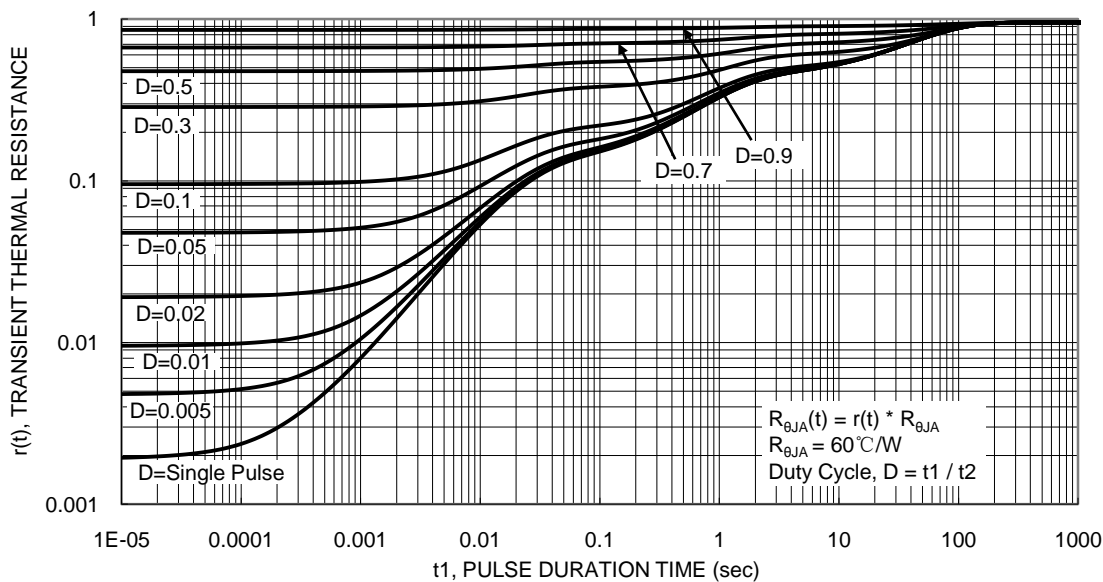
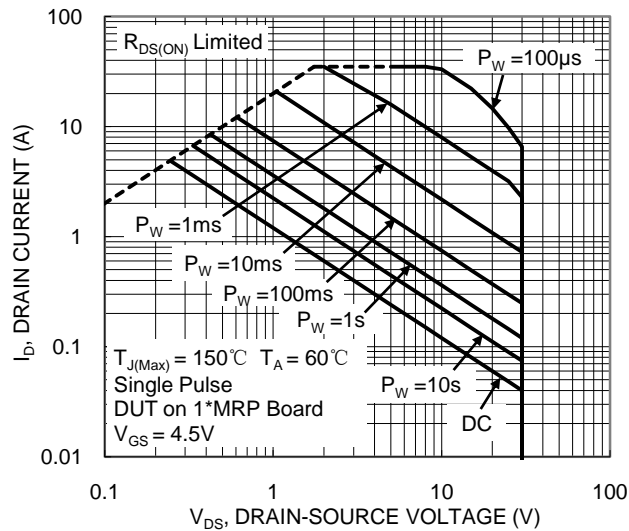
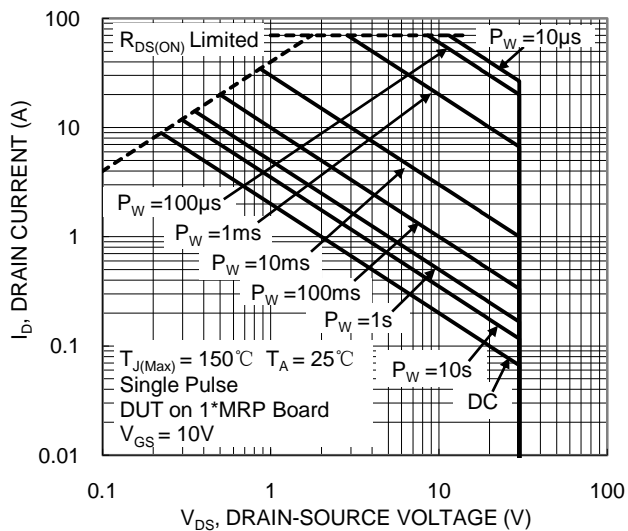
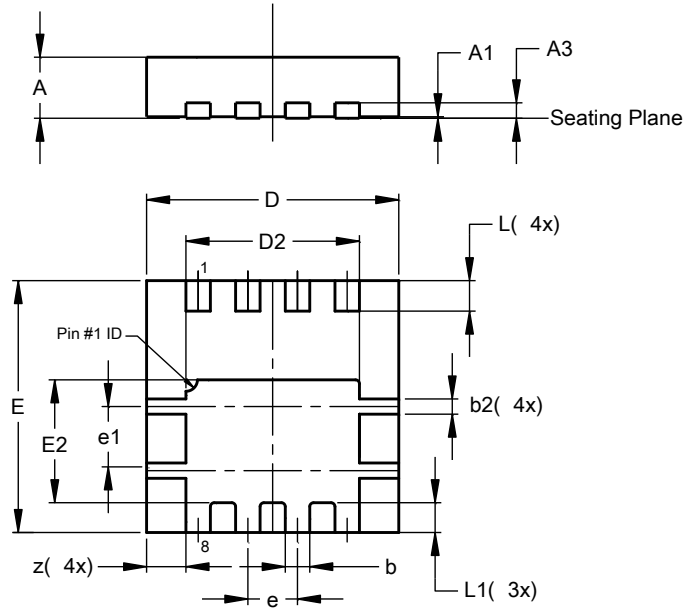


Figure 12. Single Pulse Maximum Power Dissipation



Package Outline Dimensions

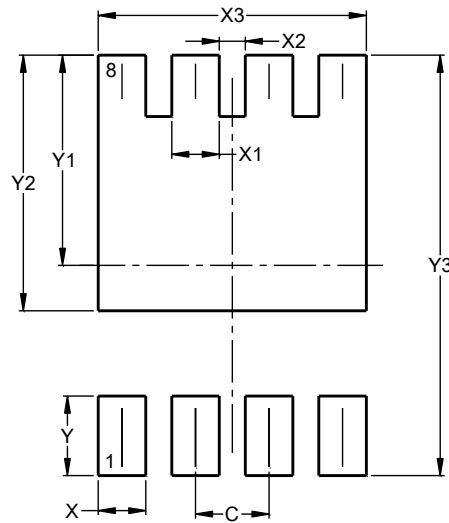
POWERDI[®] 3333-8



POWERDI [®] 3333-8			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	0.02
A3	-	-	0.203
b	0.27	0.37	0.32
b2	-	-	0.20
D	3.25	3.35	3.30
D2	2.22	2.32	2.27
E	3.25	3.35	3.30
E2	1.56	1.66	1.61
e	-	-	0.65
e1	0.79	0.89	0.84
L	0.35	0.45	0.40
L1	-	-	0.39
z	-	-	0.515
All Dimensions in mm			

Suggested Pad Layout

POWERDI[®] 3333-8



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.370
Y	0.700
Y1	1.850
Y2	2.250
Y3	3.700